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Examiner: Quyen Phan Leung

said semiconductor light emitting device further comprising a dielectric film formed on said flat portion of said cladding layer and the side surface of said ridge portion.

18. (Amended) The semiconductor light emitting device according to claim 17, wherein

said dielectric film contains a nitride on the side of the interface between said dielectric film and said side surface of said ridge portion while containing an oxide on the side opposite to said side surface of said ridge portion.

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19. (Amended) The semiconductor light emitting device according to claim 17, wherein

said dielectric film contains a compound containing nitrogen and oxygen on the side of the interface between said dielectric film and said side surface of said ridge portion while containing an oxide on the side opposite to said side surface of said ridge portion.

20. (Amended) The semiconductor light emitting device according to claim 17, wherein

said dielectric film contains a nitride on the side of the interface between said dielectric film and said side surface of said ridge portion while containing a compound containing nitrogen and oxygen on the side opposite to said side surface of said ridge portion.
